

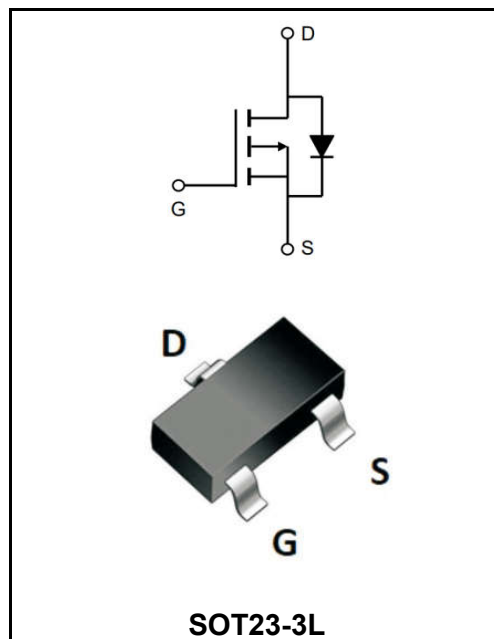
-150V P-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	-2.7A
V_{DSS}	-150V
$R_{DS(on)-typ}(@V_{GS} = -10V)$	< 780mΩ (Type: 620mΩ)

Application

- ◆ Brushless motor
- ◆ Load switch
- ◆ Uninterruptible power supply



Product Specification Classification

Part Number	Package	Marking	Pack
YFW2P15MI	SOT23-3L	2P15MI	3000PCS/Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	-150	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, $V_{GS} @ -10V^1$ @ $T_A=25^\circ C$	I_D	-2.7	A
Continuous Drain Current, $V_{GS} @ -10V^1$ @ $T_A=70^\circ C$	I_D	-1.8	A
Pulsed Drain Current ²	I_{DM}	-8.5	A
Single Pulse Avalanche Energy ³	E_{AS}	56.5	mJ
Avalanche Current	I_{AS}	5	A
Total Power Dissipation ⁴ @ $T_A=25^\circ C$	P_D	2	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	125	°C/W
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	40	°C/W

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	BV_{DSS}	-150	-168	-	V
Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-1A$	$R_{DS(ON)}$	-	620	780	mΩ
	$V_{GS}=-6V, I_D=-0.5A$		-	700	980	
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	$V_{GS(th)}$	-2.0	-3.0	-4.0	V
Drain -Source Leakage Current	$V_{DS}=120V, V_{GS}=0V, T_J=25^{\circ}C$	I_{DSS}	-	-	1	μA
	$V_{DS}=120V, V_{GS}=0V, T_J=85^{\circ}C$		-	-	30	
Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	I_{GSS}	-	-	±100	nA
Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	R_g	-	12	-	Ω
Total Gate Charge	$V_{DS}=-75V$ $V_{GS}=-10V$ $I_D=-1A$	Q_g	-	10.8	-	nC
Gate-Source Charge		Q_{GS}	-	3.1	-	
Gate-Drain Charge		Q_{gd}	-	2.2	-	
Turn-on delay time	$V_{DD}=-30V$ $V_{GS}=-10V$ $R_G=6\Omega$ $I_D=-1A$	$t_{d(on)}$	-	21	-	nS
Rise Time		T_r	-	16	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	40	-	
Fall Time		t_f	-	18	-	
Input Capacitance	$V_{DS}=-75V$ $V_{GS}=0V$ $f=1.0MHz$	C_{iss}	-	706	-	pF
Output Capacitance		C_{oss}	-	23	-	
Reverse Transfer Capacitance		C_{rss}	-	13	-	

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Ratings and Characteristic Curves

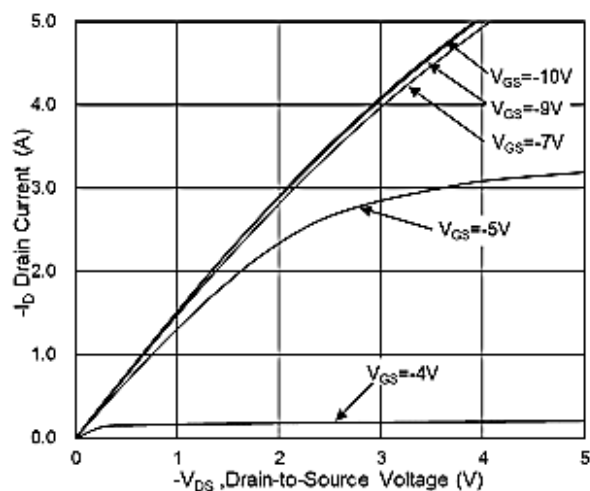


Fig.1 Typical Output Characteristics

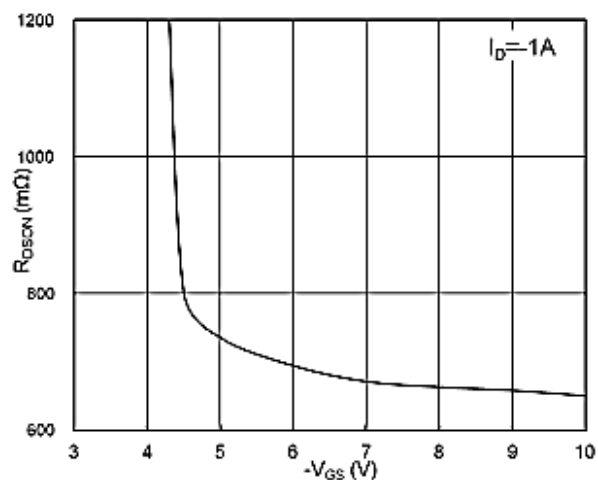


Fig.2 On-Resistance vs G-S Voltage

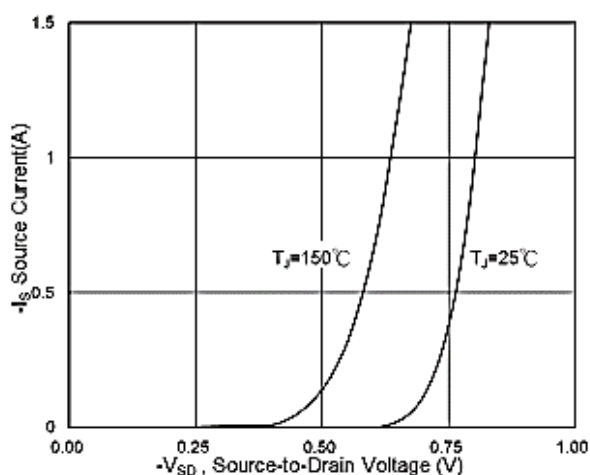


Fig.3 Source Drain Forward Characteristics

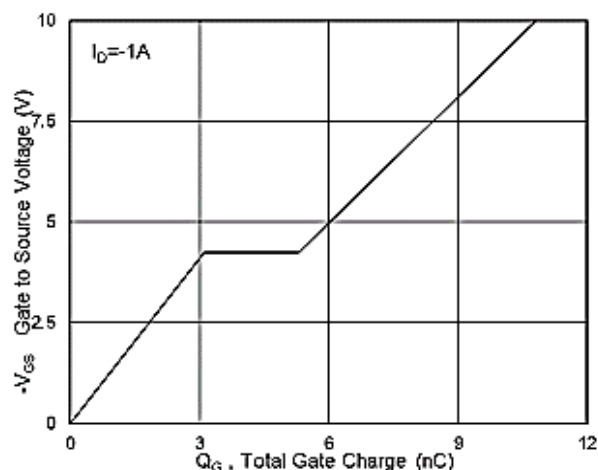


Fig.4 Gate-Charge Characteristics

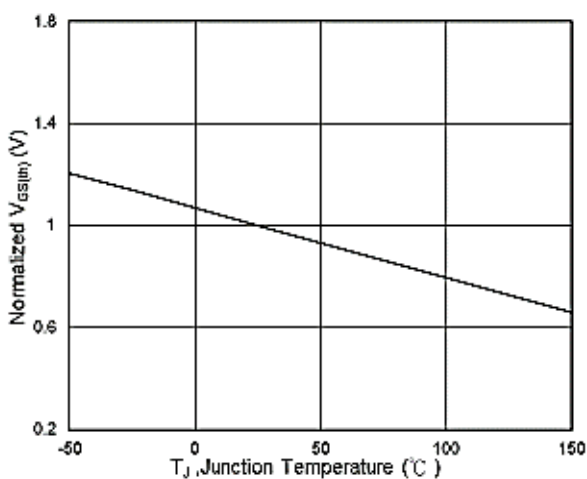


Fig.5 Normalized $V_{GS(th)}$ vs T_J

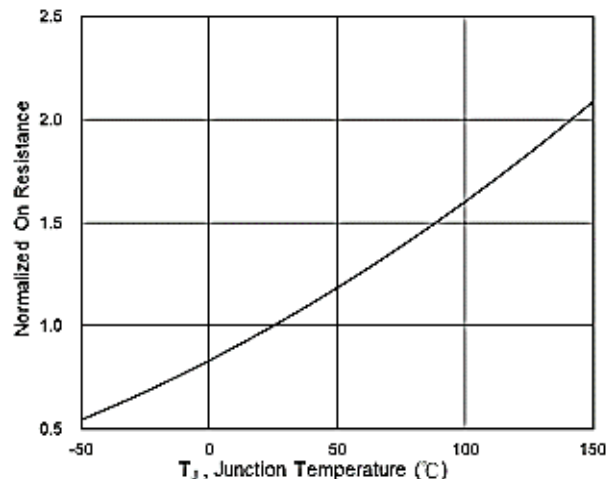


Fig.6 Normalized $R_{DS(on)}$ vs T_J

Ratings and Characteristic Curves

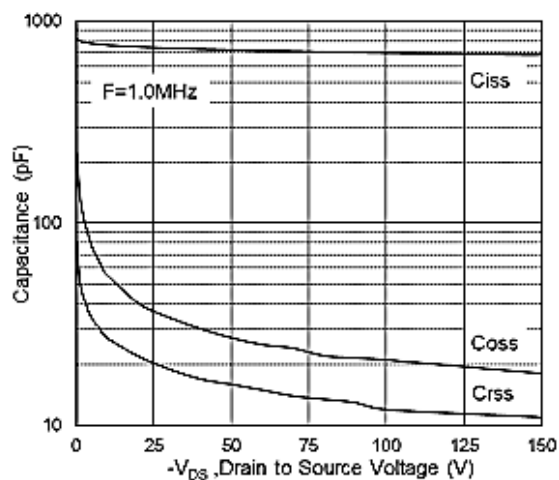


Fig.7 Capacitance

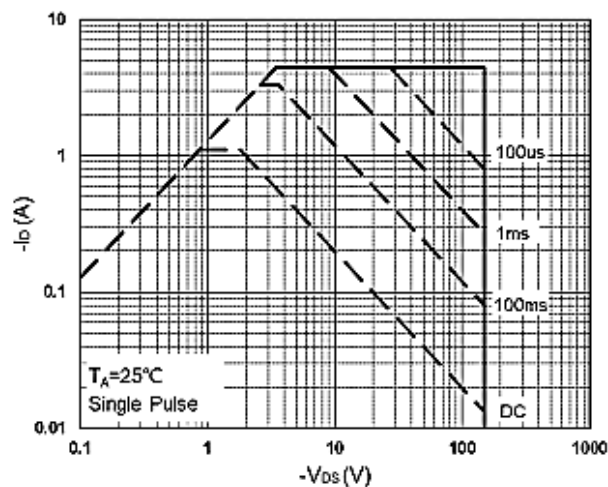


Fig.8 Safe Operating Area

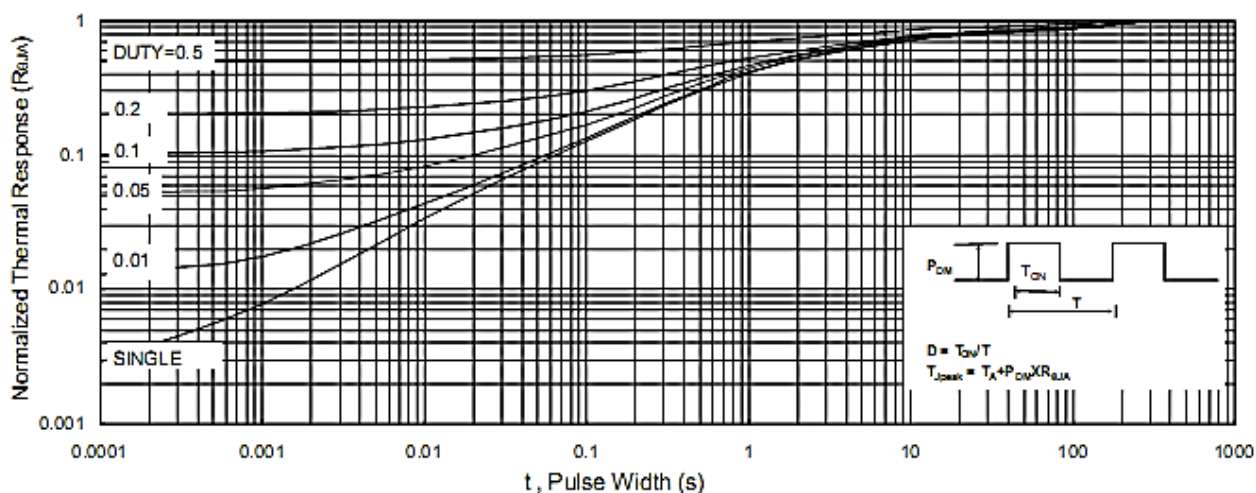


Fig.9 Normalized Maximum Transient Thermal Impedance

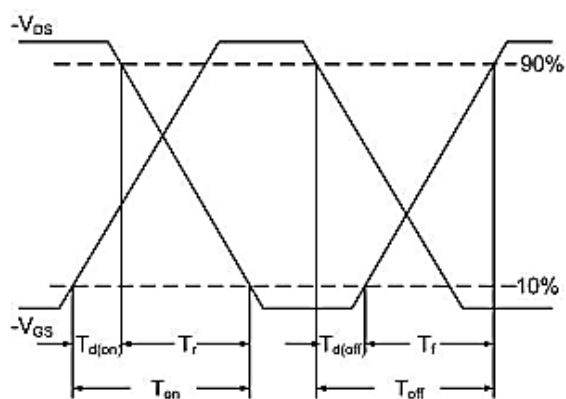


Fig.10 Switching Time Waveform

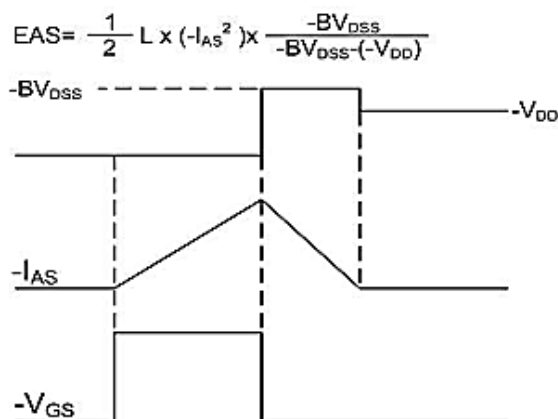
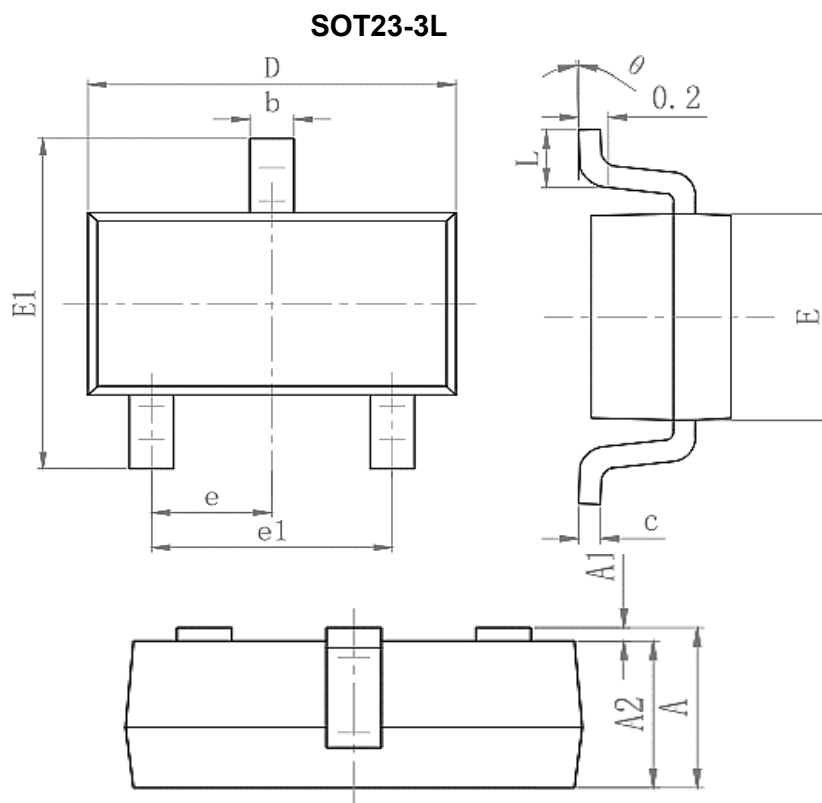


Fig.11 Unclamped Inductive Waveform

Package Outline Dimensions Millimeters



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.25	0.45
c	0.100	0.200
D	2.820	3.020
E	1.5	1.7
E1	2.650	2.950
e	0.950(BSC)	
e1	1.800	2.000
L	0.300	0.500
θ	0°	8°